MBR3035PT - MBR30200PT



30A, 35V - 200V Schottky Barrier Rectifier

FEATURES

TAIWAN

- AEC-Q101 qualified available
- Low power loss, high efficiency

MICONDUCTOR

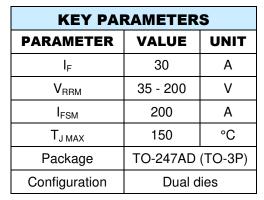
- Guard ring for overvoltage protection
- High surge current capability
- UL Recognized File # E-326243
- RoHS Compliant
- Halogen-free according to IEC 61249-2-21

APPLICATIONS

- Switching mode power supply (SMPS)
- Adapters
- Monitor
- DC to DC converters
- TV

MECHANICAL DATA

- Case: TO-247AD (TO-3P)
- Molding compound meets UL 94V-0 flammability rating
- Terminal: Matte tin plated leads, solderable per J-STD-002
- Meet JESD 201 class 2 whisker test
- Mounting torque: 1.13 N·m maximum
- Polarity: As marked
- Weight: 6.10g (approximately)

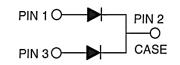






TO-247AD (TO-3P)

1



ABSOLUTE MAXIMUM RA	TINGS (T _A =	= 25°C u	inless o	therwise	e noted)					
PARAMETER	SYMBOL	MBR 3035	MBR 3045	MBR 3050	MBR 3060	MBR 3090	MBR 30100	MBR 30150	MBR 30200	UNIT
		РТ	РТ	РТ	РТ	РТ	РТ	РТ	РТ	
Marking code on the device		MBR 3035 PT	MBR 3045 PT	MBR 3050 PT	MBR 3060 PT	MBR 3090 PT	MBR 30100 PT	MBR 30150 PT	MBR 30200 PT	
Repetitive peak reverse voltage	V _{RRM}	35	45	50	60	90	100	150	200	V
Reverse voltage, total rms value	V _{R(RMS)}	24	31	35	42	63	70	105	140	V
Forward current	I _F					30				Α
Surge peak forward current 8.3ms single half sine wave superimposed on rated load	I _{FSM}				2	200				А
Peak repetitive reverse surge current ⁽¹⁾	I _{RRM}	2 1					Α			
Peak repetitive forward current (Rated V _R , Square wave, 20KHz)	I _{FRM}	30					А			

Notes:

1. tp = 2.0µs, 1.0KHz

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ABSOLUTE MAXIMUM RATINGS (T _A = 25°C unless otherwise noted)										
PARAMETER	SYMBOL	MBR 3035 PT			MBR 3060 PT		MBR 30100 PT	MBR 30150 PT	MBR 30200 PT	UNIT
Critical rate of rise of off-state voltage	dV/dt	10,000					V/µs			
Junction temperature	TJ	-55 to +150					°C			
Storage temperature	T _{STG}		-55 to +150					°C		

THERMAL PERFORMANCE			
PARAMETER	SYMBOL	ТҮР	UNIT
Junction-to-case thermal resistance	R _{eJC}	1.4	°C/W

PARAMETER		CONDITIONS	SYMBOL	ТҮР	MAX	UNIT
	MBR3035PT MBR3045PT MBR3050PT			-	- 0.75	V V
	MBR3060PT MBR3090PT MBR30100PT	$I_F = 15A, T_J = 25^{\circ}C$		-	0.85	V
	MBR30150PT			-	0.95	V
	MBR30200PT			-	1.05	V
	MBR3035PT MBR3045PT		VF	-	0.82	V
Forward voltage per diode ⁽¹⁾	MBR3050PT MBR3060PT	I _F = 30A, T _J = 25°C		-	-	V
	MBR3090PT MBR30100PT			-	-	V
	MBR30150PT			-	1.02	V
	MBR30200PT			-	1.10	V
	MBR3035PT MBR3045PT	I _F = 15A, T _J = 125°C		-	0.60	V
	MBR3050PT MBR3060PT			-	0.65	V
	MBR3090PT MBR30100PT			-	0.75	V
	MBR30150PT			-	0.92	V
	MBR30200PT			-	-	V
MBR3045P	MBR3035PT MBR3045PT			-	0.73	V
	MBR3050PT MBR3060PT			-	-	V
	MBR3090PT MBR30100PT	I _F = 30A, T _J = 125°C		-	-	V
	MBR30150PT			-	0.98	V
	MBR30200PT			-	-	V

Notes:

1. Pulse test with PW = 0.3ms



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ELECTRICAL SPECIF	ICATIONS	$(T_A = 25^{\circ}C \text{ unless otherwise})$	erwise noted)			
PARAMETER		CONDITIONS	SYMBOL	ТҮР	MAX	UNIT
MBR3035PTMBR3045PTMBR3050PTMBR3050PTMBR3060PTMBR3090PTMBR30100PTMBR30150PTMBR30150PTMBR30200PTMBR3035PTMBR3045PTMBR3050PTMBR3050PTMBR3050PTMBR3050PTMBR3050PTMBR3050PTMBR3050PTMBR3050PTMBR30100PTMBR30100PTMBR30150PTMBR30150PTMBR30200PT	T 0500		-	1000	μΑ	
	MBR30100PT	T _J = 25°C	. I _R	-	500	μA
	MBR30200PT			-	100	μA
		T _J = 125°C		-	20	mA
				-	15	mA
	MBR30100PT MBR30150PT			-	10	mA

Notes:

2. Pulse test with PW = 30ms

ORDERING INFORMATION					
ORDERING CODE ⁽¹⁾⁽²⁾	PACKAGE	PACKING			
MBR30xPT	TO-247AD (TO-3P)	30 / Tube			
MBR30xPTH	TO-247AD (TO-3P)	30 / Tube			

Notes:

1. "x" defines voltage from 35V(MBR3035PT) to 200V(MBR30200PT)

2. "H" means AEC-Q101 qualified



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CHARACTERISTICS CURVES

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$

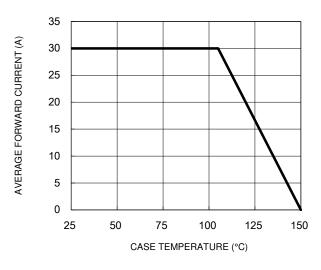


Fig.1 Forward Current Derating Curve

Fig.3 Typical Reverse Characteristics

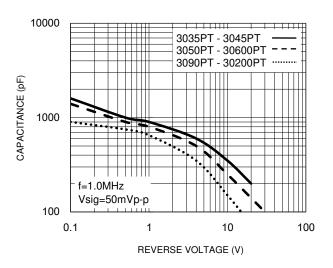
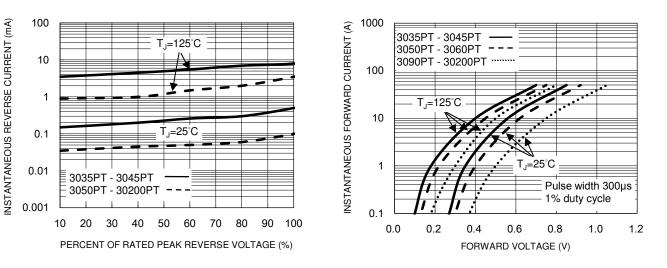


Fig.2 Typical Junction Capacitance

Fig.4 Typical Forward Characteristics



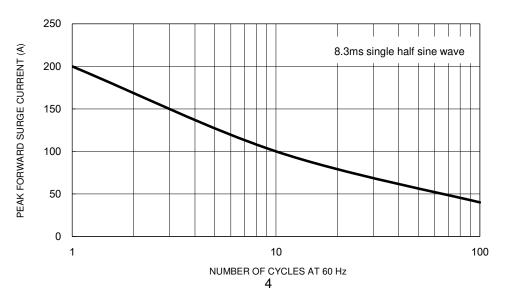


Fig.5 Maximum Non-Repetitive Forward Surge Current



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CHARACTERISTICS CURVES

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$

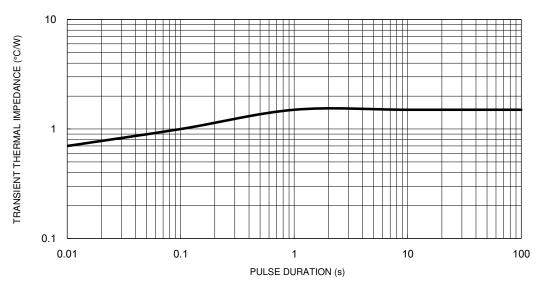


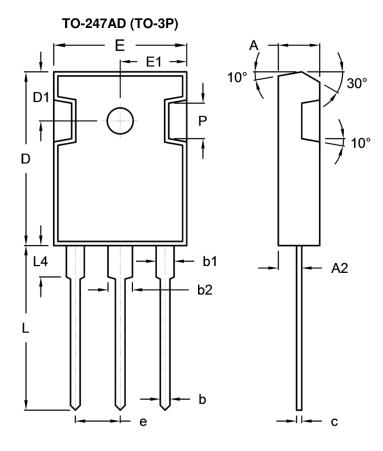
Fig.6 Typical Transient Thermal Impedance



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PACKAGE OUTLINE DIMENSIONS



DIM	Unit (mm)		Unit ((inch)
	Min	Max	Min	Max
A	4.90	5.16	0.193	0.203
A2	2.70	3.00	0.106	0.118
b	1.12	1.22	0.044	0.048
b1	1.93	2.18	0.076	0.086
b2	2.97	3.22	0.117	0.127
с	0.51	0.76	0.020	0.030
D	20.80	21.30	0.819	0.839
D1	5.70	6.20	0.224	0.244
E	15.90	16.40	0.626	0.646
E1	7.90	8.20	0.311	0.323
е	5.20	5.70	0.205	0.224
н	2.90	3.40	0.114	0.134
L	19.70	20.20	0.776	0.795
L4	3.50	4.10	0.138	0.161
Р	-	4.30	-	0.169

MARKING DIAGRAM



P/N	= Marking Code
G	= Green Compound
YWW	= Date Code

F = Factory Code



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